## Scalable Pulsed Laser Deposition of Inorganic Charge Transport Layers for Perovskite-on-Silicon Tandem Solar Cells

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The power conversion efficiency (PCE) of halogenated perovskite-on-silicon (PK/Si) tandem solar cells has recently increased from 23.6% to 33.9% on small areas<sup>[1]</sup>, exceeding the 30% theoretical limit for crystalline silicon cells. The inverted p-i-n configuration of perovskite solar cells (PSC) is ideal for tandem integration with silicon heterojunction cells, particularly due to its low fabrication temperature. This study investigates the room temperature, precursor-free deposition of  $SnO_2^{[2]}$  and  $NiO_x^{[3]}$  as inorganic electron and hole transport layers (ETL/HTL) using pulsed laser deposition (PLD). This wafer-based technique provides low substrate damage and uniform coverage across large areas, with a competitive deposition rate compared to atomic layer deposition (ALD) and RF magnetron sputtering. Non-textured PK/Si tandem cells with PLD-grown SnO<sub>2</sub> and NiO<sub>x</sub> achieved remarkable peak PCEs of 23.1% and 21.8% on a 9 cm<sup>2</sup> area under one-sun illumination, without anti-reflective coating or passivation. Perspectives include upcoming combined integration of PLD-grown selective layers and electrodes (SnO<sub>2</sub>, NiO<sub>x</sub>, ITO), as well as ongoing development of a PLD-deposited perovskite absorber. To this end, we report a first successful single junction integration of PLD-CsPbI<sub>2</sub>Br on top of PLD-NiO<sub>x</sub>.



Figure 1. a. Schematic of employed large-area pulsed laser deposition (PLD) technique, b. Monolithic PK/Si-heterojunction p-i-n tandem solar cell (9 cm<sup>2</sup> active area), c. J-V reverse curves under AM1.5
1000 W/m<sup>2</sup> of tandem cells integrating PLD-SnO<sub>2</sub> or NiO<sub>x</sub> vs lab benchmarks (forward in dotted lines) with J-V parameters summary, d. External Quantum Efficiencies of tandem cells with integrated photocurrents, e. J-V curves under one-sun of p-i-n single junction cells integrating PLD-CsPbI<sub>2</sub>Br and NiO<sub>x</sub> together, f. Stability of tandem cells in N<sub>2</sub>-storage (showing Isun illumination ageing for NiO<sub>x</sub> vs 2PACz).

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